

TSMC97-232BC

PLEASE AMEND THE CLAIMS AS FOLLOWS:

Claim 19. (previously amended) A cylindrical shaped, capacitor structure, featuring a cylindrical storage node structure comprised of an underlying, uniformly doped, cylindrical polysilicon shape and an overlying agglomerated metal silicide layer, wherein said agglomerated metal silicide layer is located only on exposed surfaces of said cylindrical polysilicon shape, comprising:

10 said cylindrical polysilicon shape comprised of a bottom polysilicon shape located on a first section of a top surface of an underlying planar, insulator layer, with said bottom polysilicon shape overlying and contacting a top surface of a plug structure which in turn is located in an opening in said insulator layer, and with said
15 cylindrical polysilicon shape comprised of uniformly doped, vertical polysilicon shapes, located overlying second sections of said planar, insulator layer, with bottom portions of said vertical polysilicon shapes butting edges of said bottom polysilicon shape;

said agglomerated metal silicide layer with a roughened top surface, located only on exposed portions of said cylindrical polysilicon shape ~~shaped storage node~~ and not located on any other surface of said cylindrical shaped,
5 capacitor structure or on any surface of said planar
insulator layer, with said ~~and featuring~~ agglomerated metal silicide on top surface of said bottom polysilicon shape, and on all surfaces of uniformly doped, said vertical polysilicon shapes, resulting in said cylindrical shape
10 storage node structure comprised ~~of~~ with said agglomerated metal silicide layer located only on said cylindrical polysilicon shape;

a capacitor dielectric layer located only on the exposed surfaces of said cylindrical polysilicon shape
15 ~~storage node structure,~~ with said capacitor dielectric
layer located only overlying said agglomerated metal
silicide layer; and

an upper electrode, covering said capacitor dielectric layer.

Claim 20 (cancelled)

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Claim 21 (currently amended) The ~~semiconductor~~ cylindrical
shaped, capacitor structure of Claim 19, wherein said
agglomerated metal silicide layer is selected from a group
consisting of titanium silicide, cobalt silicide, nickel
silicide, and platinum silicide.